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April 2017

# FPF3042 IntelliMAX™ 18 V-Rated, Dual-Input, Single-Output, Power-Source-Selector Switch

### **Features**

- Dual-Input, Single-Output Load Switch (DISO)
- Input Supply Operating Range:
  - 4.0 V~12.4 V at V<sub>IN</sub>
  - 4.0 V~12.4 V at V<sub>BUS</sub>
- Typical R<sub>ON</sub>:
  - 95 m $\Omega$  at V<sub>IN</sub>=5 V
  - 70 mΩ at V<sub>BUS</sub>=5 V
- Bidirectional Switch for VIN and VBUS
- Slew Rate Controlled:
  - 50  $\mu$ s at  $V_{IN}$  for  $< 4.7 \mu$ F  $C_{OUT}$
  - 90  $\mu$ s at V<sub>BUS</sub> for < 4.7  $\mu$ F C<sub>OUT</sub>
- Maximum I<sub>SW</sub>: 2.7 A per Channel
- Break-Before-Make Transition
- Under-Voltage Lockout (UVLO)
- Over-Voltage Lockout (OVLO)
- Thermal Shutdown
- Logic CMOS IO Meets JESD76 Standard for GPIO Interface and Related Power Supply Requirements
- ESD Protected:

Human Body Model: >3 kV
Charged Device Model: >1.5 kV
IEC 61000-4-2 Air Discharge: >15 kV

- IEC61000-4-2 Contact Discharge: >8 kV

## Description

The FPF3042 is an 18 V-rated Dual-Input Single-Output (DISO) load switch consisting of two channels of slew-rate-controlled, low-on-resistance, N-channel MOSFET switches with protection features. The slew-rate-controlled turn-on characteristic prevents inrush current and the resulting excessive voltage droop on the input power rails. The input voltage range operates from 4.0 V to 12.4 V at both  $V_{\text{BUS}}$  and  $V_{\text{IN}}$  to align with the needs of high-voltage portable device power rails.

Both  $V_{\text{IN}}$  and  $V_{\text{BUS}}$  have the over-voltage protection of 14 V (typical) to avoid damage to the system.

 $V_{\text{IN}}$  and  $V_{\text{BUS}}$  bidirectional switching allows reverse current from  $V_{\text{OUT}}$  to  $V_{\text{IN}}$  or  $V_{\text{BUS}}$  for On-The-Go, (OTG) Mode. The switching is controlled by logic input EN and  $V_{\text{IN\_SEL}}$  is capable of interfacing directly with low-voltage control signal General-Purpose Input / Output (GPIO).

FPF3042 is available in 1.76 mm x 1.96 mm Wafer-Level Chip-Scale Package (WLCSP), 16-bump, 0.4 mm pitch.

# **Applications**

- Input Power-Selection Block Supporting USB and Wireless Charging
- Smart Phone / Tablet PC

# **Ordering Information**

Part Number	Top Mark	Channel	Typical R <sub>ON</sub> per Channel at 5 V <sub>IN</sub>	Rise Time (t <sub>R</sub> )	Package
			95 m $\Omega$ for $V_{\text{IN}}$	50 $\mu s$ for $V_{IN}$	16-Bump, 1.76 mm x 1.96 mm,
FPF3042UCX	TR	DISO	70 mΩ for V <sub>BUS</sub>	90 μs for V <sub>BUS</sub>	Wafer-Level Chip-Scale Package   (WLCSP), 0.4 mm Pitch

# **Application Diagram**

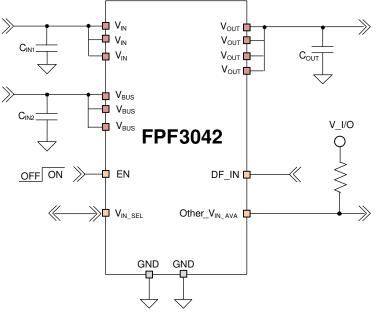


Figure 1. Typical Application

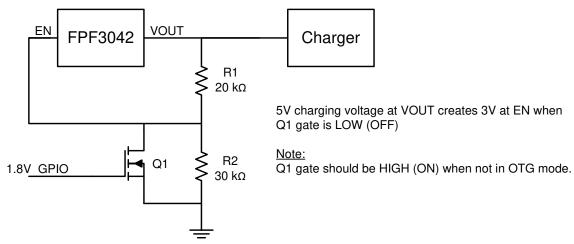


Figure 2. Example Circuit for OTG Operation with Low-Voltage GPIO

# **Block Diagram**

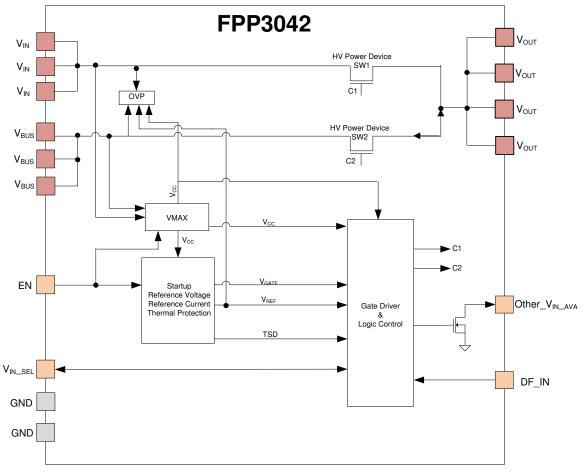


Figure 3. Functional Block Diagram

# **Pin Configuration**



Figure 4. Pin Assignment (Top View)

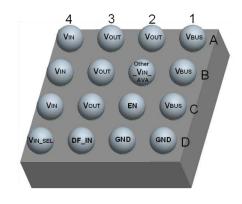


Figure 5. Pin Assignment (Bottom View)

# **Pin Description**

Pin #	Name	Input / Output	Description
A1, B1, C1	V <sub>BUS</sub>	Input / Output	V <sub>BUS</sub> at USB: Power input / output; bi-directional switch when V <sub>IN_SEL</sub> = LOW.
A4, B4, C4	V <sub>IN</sub>	Input / Output	V <sub>IN</sub> Supply Input: Power input / output; bi-directional switch when V <sub>IN_SEL</sub> = HIGH.
A2, A3, B3, C3	V <sub>OUT</sub>	Input / Output	Switch Output: Power input / output
C2	EN	Input	Enable: Active HIGH; EN voltage ≥ 2.5 V can power internal circuit when V <sub>IN</sub> and V <sub>BUS</sub> are absent. 1 MΩ pull-down resistor is included.
D4	V <sub>IN_SEL</sub>	Input / Output	Supply Selector & Status: Input power source selection input and status output. This signal is ignored during EN=LOW. Selector input during EN=HIGH: HIGH = switch V <sub>IN</sub> to V <sub>OUT</sub> / LOW = switch V <sub>BUS</sub> to V <sub>OUT</sub> . Status output during EN=LOW: HIGH = V <sub>IN</sub> is used for V <sub>OUT</sub> / LOW = V <sub>BUS</sub> is used for V <sub>OUT</sub> .
D3	DF_IN	Input	Default Supply Selector during EN=LOW: Floating = V <sub>BUS</sub> connects to V <sub>OUT</sub> . LOW = V <sub>IN</sub> connects to V <sub>OUT</sub> . This signal is ignored during EN=HIGH. 1 μA pull-up current source is included.
B2	Other_VIN_AVA	Output	Other Supply Input Status: Open-drain output.  HIGH-Z = both V <sub>IN</sub> and V <sub>BUS</sub> are valid.  LOW = the other power source is not valid.
D1, D2	GND		Ground

Table 1. **Truth Table** 

EN	V <sub>IN</sub> >V <sub>UVLO</sub>	V <sub>BUS</sub> >V <sub>UVLO</sub>	V <sub>IN_SEL</sub>	DF_IN	Other_V <sub>IN_AVA</sub>	V <sub>out</sub>	Comment
HIGH	Х	Х	LOW	Х	HI-Z if VIN & VBUS > VUVLO LOW if VIN or VBUS < VUVLO	V <sub>BUS</sub>	Vout is selected by
HIGH	Х	Х	HIGH	Х	HI-Z if V <sub>IN</sub> & V <sub>BUS</sub> >V <sub>UVLO</sub> LOW if V <sub>IN</sub> or V <sub>BUS</sub> <v<sub>UVLO</v<sub>	V <sub>IN</sub>	Bidirectional channel
LOW	YES	NO	HIGH	Х	LOW	$V_{IN}$	Automatic selection to
LOW	NO	YES	LOW	Х	LOW	$V_{BUS}$	valid input V <sub>IN_SEL</sub> is output.
LOW	YES	YES	LOW	Floating	HIGH-Z	$V_{BUS}$	V <sub>OUT</sub> is selected by
LOW	YES	YES	HIGH	LOW	HIGH-Z	V <sub>IN</sub>	DF_IN V <sub>IN_SEL</sub> is output.
LOW	NO	NO	NO	Х	Floating	Floating	OFF

### Notes:

- Internal pull-down at EN.
   1 μA pull-up current source at DF\_IN.

# **Absolute Maximum Ratings**

Stresses exceeding the Absolute Maximum Ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Parameters				
	V. V. to CND	-1.4	18.0			
.,,	V <sub>IN</sub> , V <sub>BUS</sub> to GND Pulsed, 100 ms Maximum Non-Repetitive				10.0	.,
V <sub>PIN</sub>	V <sub>OUT</sub> to GND <sup>(3)</sup>			-0.3	16.0	V
	EN, DF_IN, V <sub>IN_SEL</sub> , Ot	her_V <sub>IN_AVA</sub> to GND		-0.3	6.0	
			T <sub>A</sub> =25°C		2.70	
	Maximum Continuous Switch Current per Channel				2.70	
Isw	Maximum Continuous	T <sub>A</sub> =75°C		2.50	A	
	T <sub>A</sub> =85°C				2.25	
tpD	Total Power Dissipatio	n at T <sub>A</sub> =25°C		2.25	W	
TJ	Operating Junction Te	mperature		-40	+150	°C
T <sub>STG</sub>	Storage Junction Temp	perature	erature			
ӨЈА	Thermal Resistance, J	unction-to-Ambient (1in. Square	Pad of 2 oz. Copper)		55 <sup>(4)</sup>	°C/W
		Human Body Model, ANSI/ESDA/JEDEC JS-001-2012				
	Electrostatic Discharge Capability	Charged Device Model, JESD22-C101				
ESD		IEC61000-4-2 System Level <sup>(5)</sup>	Air Discharge (V <sub>IN</sub> , V <sub>BUS</sub> to GND)	15.0		kV
		TEGO 1000-4-2 System Levers	Contact Discharge (V <sub>IN</sub> , V <sub>BUS</sub> to GND)	8.0		

### Notes:

- 3. If an external voltage of more than 13 V is applied to  $V_{OUT}$ , the slew rate should be <1 V/ms from 13 V.
- 4. Measured using 2S2P JEDEC standard PCB.
- 5. System-level ESD can be guaranteed by design.

# **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameters	Min.	Max.	Unit
\/	V <sub>IN</sub>	4.0	12.4	\/
V <sub>PIN</sub>	V <sub>BUS</sub>	4.0	12.4	V
TA	Ambient Operating Temperature	-40	+85	°C

## **Electrical Characteristics**

 $V_{\text{IN}}$ =4 to 12.4 V,  $V_{\text{BUS}}$ =4 to 12.4 V,  $T_{\text{A}}$ =-40 to 85°C unless otherwise noted. Typical values are at  $V_{\text{IN}}$ = $V_{\text{BUS}}$ =5 V, EN=HIGH and  $T_{\text{A}}$ =25°C unless otherwise noted.

Symbol	Parameters	Condition	Min.	Тур.	Max.	Unit
VIN	Input Voltage from V <sub>IN</sub>		4.0		12.4	٧
V <sub>BUS</sub>	Input Voltage from V <sub>BUS</sub>		4.0		12.4	V
	0 : .0 .	I <sub>OUT</sub> =0 mA, EN=HIGH, V <sub>IN</sub> or V <sub>BUS</sub> =5 V		55	120	μA
la	Quiescent Current	I <sub>OUT</sub> =0 mA, EN=5 V, V <sub>IN</sub> and V <sub>BUS</sub> =GND		33	70	μΑ
		V <sub>IN</sub> =12 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		95		
		V <sub>IN</sub> =8 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		95		
	On Resistance for V <sub>IN</sub>	V <sub>IN</sub> =5 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		95	150	mΩ
Б		V <sub>IN</sub> =5 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C to 85°C <sup>(6)</sup>			200	
Ron		V <sub>BUS</sub> =12 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		70		
		V <sub>BUS</sub> =6 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		70		
	On Resistance for V <sub>BUS</sub>	V <sub>BUS</sub> =5 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		70	100	mΩ
		V <sub>BUS</sub> =5 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C to 85°C <sup>(6)</sup>			140	
V <sub>IH</sub>	Input Logic High Voltage	V <sub>IN</sub> , V <sub>BUS</sub> = 4.0 V~12.4 V	1.15			V
VIL	Input Logic Low Voltage	V <sub>IN</sub> , V <sub>BUS</sub> =4.0 V~12.4 V			0.52	٧
V <sub>EN(OTG)</sub>	EN Voltage in OTG Mode <sup>(6)</sup>	Vin & Vbus=Float or Vin & Vbus < Vuvlo	2.5			V
R <sub>EN_PD</sub>	Pull-Down Resistance at EN			1000		kΩ
Protectio	n					
V	Linder Voltage Leekeut Threehold	V <sub>IN</sub> or V <sub>BUS</sub> Rising	3.05	3.50	4.00	V
Vuvlo	Under-Voltage Lockout Threshold	V <sub>IN</sub> or V <sub>BUS</sub> Falling	2.55	3.00	3.55	٧
Vuvhys	Under-Voltage Lockout Hysteresis			0.5		٧
		V <sub>IN</sub> Rising Threshold	12.9	14.0	15.0	٧
Vovlo	Over-Voltage Lockout Threshold	V <sub>IN</sub> Falling Threshold	12.4	13.5	14.5	V
VOVLO		V <sub>BUS</sub> Rising Threshold	12.9	14.0	15.0	V
		V <sub>BUS</sub> Falling Threshold	12.4	13.5	14.5	V
Voveys	Over-Voltage Lockout Hysteresis	Vin		0.5		V
VOVHYS	Over-voltage Lockout Hysteresis	V <sub>BUS</sub>		0.5		V
T <sub>SDN</sub>	Thermal Shutdown Threshold			150		°C
T <sub>SDNHYS</sub>	Thermal Shutdown Hysteresis			20		°C
Reverse (	Current Blocking (RCB)					
I <sub>RCB</sub>	VIN or VBUS Current During RCB	V <sub>OUT</sub> =8 V, V <sub>IN</sub> or V <sub>BUS</sub> =GND			30	μΑ
Dynamic	Characteristics					
+_	Vout Rise Time, V <sub>BUS</sub> (6,7)			90		μs
t <sub>R</sub>	V <sub>OUT</sub> Rise Time, V <sub>IN</sub> (6.7)	V V 5V D 4500 0 47 5		50		
tғ	V <sub>OUT</sub> Fall Time <sup>(6,7)</sup>	$V_{IN}=V_{BUS}=5$ V, $R_{L}=150$ $\Omega$ , $C_{L}=4.7$ $\mu F$ , $T_{A}=25$ °C		1.4		ms
ttran	Transition Delay(6,7)		50	100		ms
t <sub>SD</sub>	Selection Delay(6,7)			50		μs

### Notes:

- 6. This parameter is guaranteed by characterization and/or design; not production tested.
- 7. t<sub>SD</sub>/t<sub>TRAN</sub>/t<sub>R</sub>/t<sub>F</sub> are defined in Figure 6.

# Timing Diagram

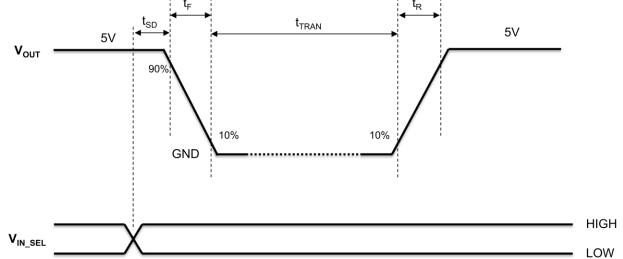
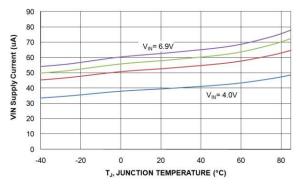


Figure 6. Transition Delay ( $V_{IN}=V_{BUS}=5~V$ )

# **Typical Characteristics**



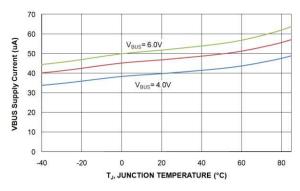
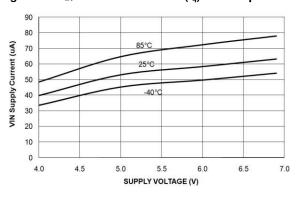


Figure 7. VIN Quiescent Current (Ia) vs. Temperature Figure 8. VBUS Quiescent Current (Ia) vs. Temperature



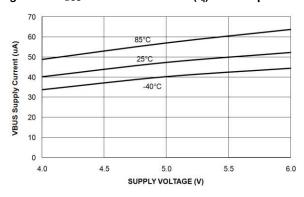


Figure 9. V<sub>IN</sub> Quiescent Current vs. Supply Voltage

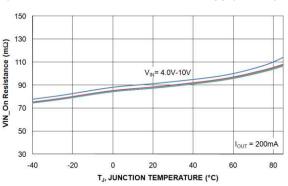


Figure 10. V<sub>BUS</sub> Quiescent Current vs. Supply Voltage

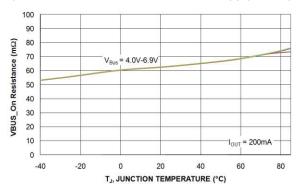


Figure 11.  $V_{IN}$  On Resistance (m $\Omega$ ) vs. Temperature

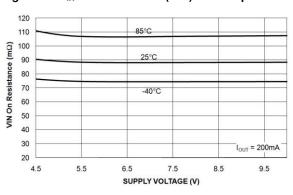


Figure 12.  $V_{BUS}$  On Resistance (m $\Omega$ ) vs. Temperature

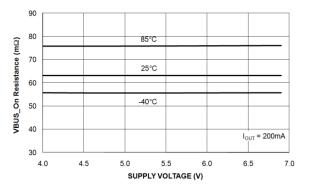


Figure 13.  $V_{IN}$  On Resistance (m $\Omega$ ) vs. Supply Voltage Figure 14.  $V_{BUS}$  On Resistance (m $\Omega$ ) vs. Supply Voltage

# Typical Characteristics (Continued)

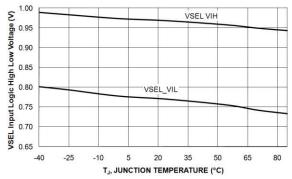
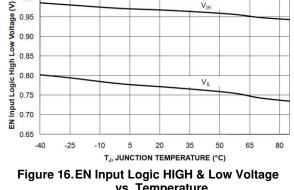


Figure 15.V<sub>IN</sub>\_SEL Input Logic HIGH & Low Voltage vs. Temperature



1.00

vs. Temperature

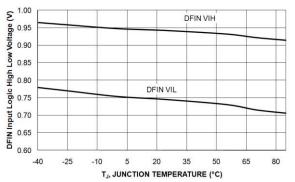


Figure 17.DF\_IN Logic HIGH & Low Voltage vs. Temperature

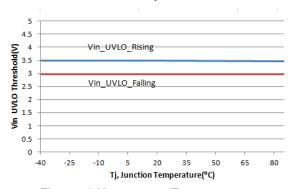


Figure 18. V<sub>IN\_VULVO</sub> vs. Temperature

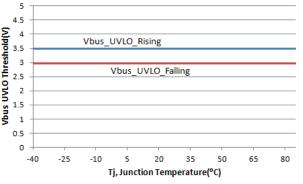


Figure 19. VBUS\_VULVO vs. Temperature

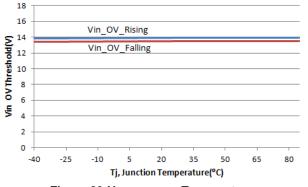


Figure 20. VIN\_VOVLO vs. Temperature

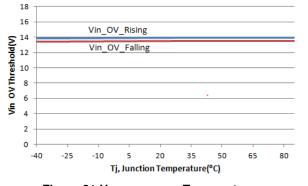


Figure 21. V<sub>BUS\_VOVLO</sub> vs. Temperature

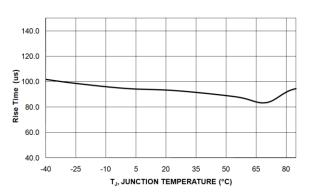
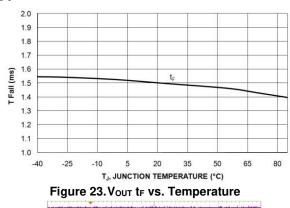
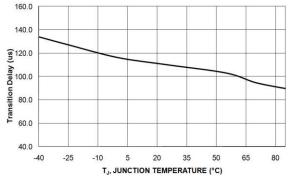


Figure 22. Vout t<sub>R</sub> vs. Temperature



Typical Characteristics (Continued)



Other\_Vin\_Ava [5V/div]

VIN\_SEL [5V/div]

VOUT [2V/div]

Figure 24.ttran vs. Temperature

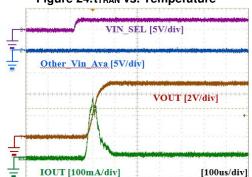
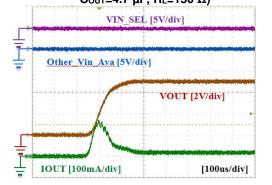


Figure 25. Power Source Transition (V<sub>IN</sub>=V<sub>BUS</sub>=5 V, EN=HIGH, V<sub>IN</sub>\_SEL=LOW→HIGH→LOW, C<sub>OUT</sub>=4.7 μF, R<sub>L</sub>=150 Ω)

IOUT [100mA/div]

[100ms/div]

Figure 26. V<sub>IN</sub> On Response (V<sub>IN</sub>=GND→5 V, V<sub>BUS</sub>=EN=GND, C<sub>OUT</sub>=4.7 μF, R<sub>L</sub>=150 Ω)



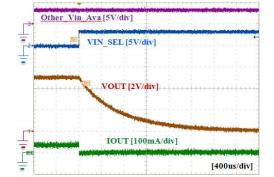
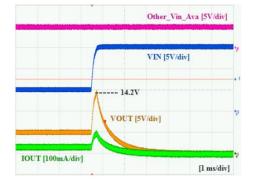


Figure 27.V<sub>BUS</sub> On Response (V<sub>BUS</sub>=GND $\rightarrow$ 5 V, V<sub>IN</sub>=EN=GND, C<sub>OUT</sub>=4.7  $\mu$ F, R<sub>L</sub>=150  $\Omega$ )

Figure 28.Off Response (V<sub>IN</sub>=V<sub>BUS</sub>=5 V, EN=HIGH, V<sub>IN</sub>\_SEL=LO $\rightarrow$ HIGH or HIGH $\rightarrow$ LOW, C<sub>OUT</sub>=4.7  $\mu$ F, R<sub>L</sub>=150  $\Omega$ )



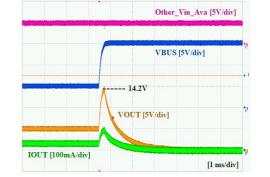


Figure 29.V<sub>IN</sub> Over-Voltage Protection Response (V<sub>IN</sub>=5 V→15 V, V<sub>BUS</sub>=5 V, EN=V<sub>IN</sub>\_SEL=HIGH, C<sub>OUT</sub>=4.7 μF, R<sub>L</sub>=150 Ω)

Figure 30. V<sub>BUS</sub> Over-Voltage Protection Response (V<sub>BUS</sub>=5 V→15 V, V<sub>IN</sub>=5 V, EN=HIGH, V<sub>IN</sub>\_SEL=LOW, C<sub>OUT</sub>=4.7 μF, R<sub>L</sub>=150 Ω)

# **Operation and Application Information**

The FPF3042 is an 18 V, 2.7 A-rated, Dual-Input Single-Output (DISO) N-channel MOSFET load switch with slew-rate-controlled and low on resistance. The input operating range is from 4 V to 12.4 V at V $_{\rm BUS}$  and at V $_{\rm IN}$ . The internal circuitry is powered from the highest voltage source among V $_{\rm IN}$ , V $_{\rm BUS}$ , and EN.

### Input Power-Source Selection

The input power source can be selected by  $V_{\text{IN\_SEL}}$  and DF\_IN, respectively, depending on the EN state. When EN is HIGH, the input source is selected by  $V_{\text{IN\_SEL}}$  regardless of DF\_IN. If  $V_{\text{IN\_SEL}}$  is LOW,  $V_{\text{BUS}}$  is selected. If  $V_{\text{IN\_SEL}}$  is HIGH,  $V_{\text{IN}}$  is selected.

Table 2. Input Power Selection by VIN SEL

EN	V <sub>IN</sub> >V <sub>UVLO</sub>	V <sub>BUS</sub> >V <sub>UVLO</sub>	V <sub>IN_SEL</sub>	DF_IN	V <sub>OUT</sub>
HIGH	Х	Х	LOW	X	$V_{\text{BUS}}$
HIGH	Х	Χ	HIGH	Х	VIN

When EN is LOW, the input source is selected by DF\_IN and the number of valid input sources. If only one input source is valid (greater than  $V_{\text{UVLO}(\text{MAX})}$ ), the source is selected automatically, regardless of DF\_IN, to make charging path in case the battery is depleted. If both  $V_{\text{BUS}}$  and  $V_{\text{IN}}$  have valid input sources, the input source is selected by DF\_IN. If DF\_IN is LOW,  $V_{\text{IN}}$  is selected. If DF\_IN is HIGH or floating,  $V_{\text{BUS}}$  is selected. DF\_IN is biased HIGH with an internal 1  $\mu\text{A}$  pull-up current source.

Table 3. Input Power Selection by DF IN

EN	$V_{IN} > V_{UVLO}$	$V_{\text{BUS}} \!\!>\!\! V_{\text{UVLO}}$	$V_{\text{IN\_SEL}}$	DF_IN	$V_{\text{OUT}}$
LOW	YES	NO	HIGH	Χ	VIN
LOW	NO	YES	LOW	Х	V <sub>BUS</sub>
LOW	YES	YES	LOW	Floating	V <sub>BUS</sub>
LOW	YES	YES	HIGH	LOW	VIN
LOW	NO	NO	Χ	Χ	Floating

 $V_{IN\_SEL}$  can be the status output to indicate which input power source is used during EN is LOW. If  $V_{IN}$  is used,  $V_{IN\_SEL}$  shows HIGH. If  $V_{BUS}$  is used,  $V_{IN\_SEL}$  shows LOW. The voltage level of HIGH signal is 5.3 V if any one of  $V_{IN}$ ,  $V_{BUS}$ , or EN is higher than 5.3 V. The signal

is highest voltage among  $V_{\text{IN}}$ ,  $V_{\text{BUS}}$ , and EN if none of them is higher than 5.3 V.

### **EN Voltage for Control Logic Power Supply**

Internal control logic is powered from the highest voltage among  $V_{\text{IN}}$ ,  $V_{\text{BUS}}$ , and  $V_{\text{EN}}$ . If valid  $V_{\text{IN}}$  or  $V_{\text{BUS}}$  higher than UVLO is applied, ON/OFF control by EN should be accomplished with  $V_{\text{IH}}/V_{\text{IL}}$ . If EN powers the internal control block without valid  $V_{\text{IN}}$  and  $V_{\text{BUS}}$ , more than 2.5 V is required on the EN pin to operate properly.

### Over-Voltage Protection (OVP)

The FPF3042 includes over-voltage protection at both  $V_{\text{IN}}$  and  $V_{\text{BUS}}$ . If  $V_{\text{IN}}$  or  $V_{\text{BUS}}$  is higher than 14 V (typical), the power switch is off until input voltage is lower than the over-voltage trip level by a hysteresis voltage of 0.5 V.

### **Reverse Power Supply for OTG**

The bidirectional switch allows reverse power for On-The-Go (OTG) operation. Even if both  $V_{\text{IN}}$  and  $V_{\text{BUS}}$  are unavailable, reverse power can be supported if internal control circuitry is powered by EN.

### **Reverse-Current Blocking (RCB)**

FPF3042 supports reverse-current blocking during EN LOW and an unselected channel.

### **Thermal Shutdown**

During thermal shutdown, the power switch is turned off if junction temperature exceeds 150°C to avoid damage.

### **Wireless Charging System**

FPF3042 can be used as an input power selector supporting Travel Adaptor (TA) and Wireless Charging (WC) with a single-input-based battery charger or Power Management IC (PMIC), including a charging block as shown in Figure 31. The system can recognize an input power source change between 5 V TA and 5 V WC without detection circuitry because FPF3042 has a 100 ms transition delay. OTG Mode can be supported without an additional power path, such as a MOSFET.

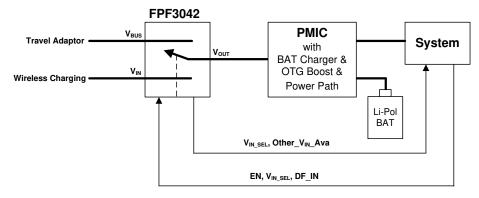
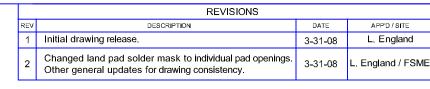
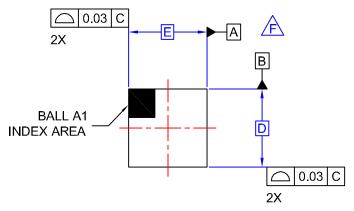


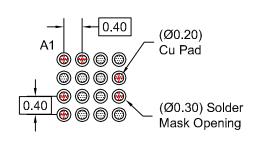
Figure 31.Input Power Selector for Wireless Charging System

# **Product Specific Package Information**

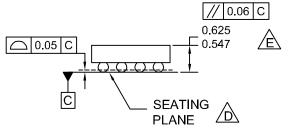
D	E	X	Υ
1.96 mm ±0.03 mm	1.76 mm ±0.03 mm	0.28 mm	0.38 mm

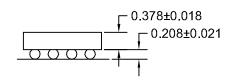






TOP VIEW RECOMMENDED LAND PATTERN (NSMD PAD TYPE)

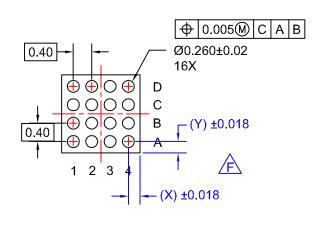




SIDE VIEWS

# NOTES:

- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCE PER ASME Y14.5M, 1994.
- DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.
- PACKAGE NOMINAL HEIGHT IS 586 MICRONS ±39 MICRONS (547-625 MICRONS).
- F. FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATASHEET.
  - G. DRAWING FILNAME: MKT-UC016AArev2.



**BOTTOM VIEW** 



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